# Indirect M n-M n pair interaction induces pseudogap in A 1(Si)-M n approxim ants

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2002/9/6

The e ect on the electronic structure of an indirect M n-M n interaction mediated by the valence states and the sp-d hybridisation is presented. In A l(rich)-M n phases related to quasicrystals (A  $l_{12}$ M n, o-A  $l_{6}$ M n, -A  $l_{6}$ M n, call M n. This indirect interaction creates a H um e-R othery pseudogap in the density of states together with a m inim isation of the band energy. It is shown that the M n-M n interaction up to the distance around 10-20 A plays an essential role in stabilizing related quasicrystal structures.

K eywords: Q uasicrystal; A pproxim ant; H um e-R othery stabilization; P seudogap; T ransition-m etal.

### 1. Introduction

A l(rich)-M n and A l(rich)-SiM n system s, contain m any crystalline approxim ants of quasicrystals. These phases are good examples to analyse the e ect of the position of transition m etal (TM) atom s in stabilizing complex structure related to quasiperiodicity. The origin of the stabilization of quasicrystals is still unclear in spite of many experimental and theoretical study. For A Hoased quasicrystals, a Hume-Rothery mechanism [1, 2] have been shown to play a signicant role (see for instance [3, 4, 5] and Refs. within). In these phases, the average number of electron per atom (ratio e=a) is an important parameter. Indeed,

Tel: 33 1 34 25 69 65 Fax: 33 1 34 25 70 04 guy.tram.bly@.ptm.u-cergy.fr explained by the fact that they are electron compounds with similar e-a ratio in spite of dierent constituents and dierent atom ic concentrations [6, 7]. A band energy minimisation occurs when the Ferm isphere touches a pseudo-Brillouin zone, constructed by Bragg vectors K  $_{\rm p}$  corresponding to intense peaks in the experimental diraction pattern. The Hume-Rothery condition for alloying is then  $2k_{\rm F}$  ' K  $_{\rm p}$ . Assuming a free electron valence band, the Fermim on entum,  $k_{\rm F}$ , is calculated from e-a.

the occurrence of phases related to quasicrystals is

In sp Hum e-R othery alloys, valence electrons (sp electrons) are nearly free. Their density of states (DOS) is well described by the Jones theory [1, 2]. The Ferm i-sphere/pseudo-Brillouin zone interaction creates a depletion in the DOS, called pseudogap, near the Ferm i energy  $E_{\rm F}$ . Such a pseudogap has been found experim entally and from rst-principles calculations in many sp quasicrystals and approximants [8, 9, 5]. It has also been

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found in many icosahedralapproximants containing TM elements [10,11,5] whereas there are contradictory results about decagonal phases (Ref. [12] and Refs. within). But, the treatment of Al(rich)-TM is more complicated as distates of TM are not nearly-free states. In the case of crystals and icosahedral quasicrystals it has been shown [13,14] that sp-d hybridisation increases a pseudogap. In some particular cases a pseudogap may also be induced by the sp-d hybridisation [15,18].

The Hume-Rothery stabilization can also be viewed as a consequence of oscillating pair interactions between atoms (Refs. [3, 19] and Refs. in there). In this direction Zou and Carlsson have shown that an indirect M n-M n interaction, mediated by sp states of A l, is strong enough to favours Mn-Mn distances close to 4.7A in Al(rich)-Mn quasicrystals and approximants. Here, it is shown that an indirect M n-M n interaction up to 10-20A induces pseudogap at E<sub>F</sub> in the approximants: cubic A 1<sub>12</sub>M n [14], orthorhom bic o-A 1<sub>6</sub>M n [14], and cubic -A l<sub>9</sub>M n<sub>2</sub>Si [20]. The importance of Mn-Mn interaction up to large distances shows the complexity of the stabilizing process. Obviously \frustration" mechanism should occur that may favour for complex atomic structures. As  $A \downarrow_{12} M n$ , o- $A \downarrow_{6} M n$  and - $A \downarrow_{9} M n_{2} Si$  are related to quasicrystals, this study suggests that a Hume-Rothery stabilization, expressed in terms of M n-M n interaction, is intrinsically linked to the em ergence of quasiperiodic structures in A 1(Si)-M n system s.

## 2. E ective B ragg potential for A l(rich)-M n alloys

For sp H um e-R othery alloys, the valence states (sp states) are nearly-free states scattered by a weak potential (B ragg potential,  $V_B$ ). In this section, we show brie y that in sp-d H um e-R othery alloys, sp electrons feel an \e ective B ragg potential" [14, 12] that takes into account the strong e ect TM atom s via the sp-d hybridisation.

Following a classical approximation [16,17] for

A l(Si)-M n alloys, a simpli ed model is considered where sp states are nearly-free and d states are localized on M n sites i. The e ective ham iltonian for the sp states is written:

$$H_{eff(sp)} = \frac{h^2 k^2}{2m} + V_{B;eff}$$
 (1)

where  $V_{\text{B};eff}$  is an elective B ragg potential that takes into account the scattering of sp states by the strong potential of M n atom s.  $V_{\text{B};eff}$  depends thus on the positions  $r_{i}$  of M n atom s. A ssum ing that all M n atom s are equivalent and that two M n atom s are not instanced in rst-neighbour, one obtains [14,12]:

$$V_{B \text{ ;eff}}(\mathbf{r}) = X$$

$$V_{B \text{ ;eff}}(K) e^{iK : \mathbf{r}}; \quad (2)$$

$$V_{B \text{ ;eff }}(K) = V_{B}(K) + \frac{j_{K} j_{d}}{E E_{d}} = e^{iK : r_{i}};$$
 (3)

where the vectors K belong to the reciprocal lattice,  $t_K$  is a average m atrix element that couples sp states k and k K via the sp-d hybridisation, and E d is the energy of d states. The term  $V_B$  (K) is a weak potential independent with the energy E . It corresponds to the B ragg potential for sp H um e-R othery compounds.

The last term in equation (3), is due to the d resonance of the wave function by the potential of M n atom s. It is strong in an energy range  $E_d = E_d +$ , where 2 is the width of the d resonance. This term is essential as it does represent the di raction of the sp electrons by a network of d orbitals, i.e. the factor  $e^{iK \cdot r_1}$  corresponding to the structure factor of the TM atom s sub-lattice. A s the d band of M n is almost half lled,  $E_F = E_d$ , this factor is important for energy close to  $E_F = E_d$ . Note that the B ragg planes associated with the second term of equation (3) correspond to B ragg planes determ ined by di raction.

This analysis shows that both sp-d hybridisation and direction of sp states by the sub-lattice of M n atoms are essential to understand the electronic structure of Al(Si)-M n alloys [12]. The strong e ect of sp-d hybridisation on the pseudogap is then understood in the fram ework of Hume-Rothery mechanism.

#### 3. Two M n in the A l(Si) m atrix

As a Hume-Rothery stabilization is a consequence of oscillation of the charge density of the valence electrons with energy close to  $E_F$  , a most stable atom ic structure is obtained when distances between atoms are multiples of the wavelength of electrons with energy close to  $E_{\,\mathrm{F}}$  . Since the scattering of valence sp states by the M n sub-lattice is strong, the Friedel oscillations of charge of sp electrons around M n m ust have a strong e ect on a stabilization. Therefore a Hume-Rothery mechanism in Al(rich)-Mn compounds might be analysed in term of a M n-M n pair interaction resulting from a strong sp-d hybridisation. Zou and Carlsson [21, 22] have calculated this interaction from an Anderson modelham iltonian with two impurities, using a G reen's function m ethod. It is found that a speci c M n-M n distance of 4.7A favours for a stabilization of A LM n approxim ants [21]. As 4.7A is larger than rst neighbour distances, this shows the existence of an indirect medium range Mn-Mn interaction. The indirect interaction is mediated by sp-d hybridisation where sp states are mainly Alstates.

W e calculated the indirect M n-M n pair interaction  $M n \rightarrow M n$  from the transfer matrix T of two M n atoms in the free electrons matrix by using the Lloyd formula [23] (Fig.1). A coording to classical approximation for metal, a phenomenological short range repulsive term should be add. But this term is not important in the present study as we analyse only the medium range order, i.e. distances larger than rst-neighbour distances (see Fig.1). Param eters of the calculation are: the Fermi energy  $E_F$  xed by the Alma $trix (E_F = 11.7 eV)$ , the width of the d resonance 2 which increases as the sp-d hybridisation increases (2 =  $2.7 \,\mathrm{eV}$ ), and the energy  $E_{\mathrm{d}}$ of the d resonance which depends on the nature of the transition m etal atom  $(E_d = 11.37 \, eV \, cor$ responding to 5.8 d electrons per M n atom). A small variation of these parameters does not modify qualitatively the results presented in the following. In this paper only non-magnetic Mn are considered as most of M n are non-magnetic in quasicrystals and approximants [24, 25, 26]. In

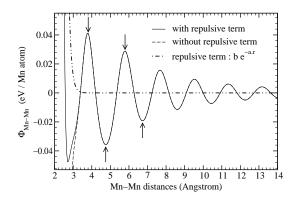


Fig. 1: M n-M n pair interaction of two non-magnetic manganese atoms in free electron matrix, simulating aluminium (and silicon) host.  $2 = 2.7\,\text{eV}$ ,  $E_\text{d} = 11.37\,\text{eV}$  and  $E_\text{F} = 11.7\,\text{eV}$ .

particular A  $l_{12}$ M n, o-A  $l_{6}$ M n and -A  $l_{9}$ M  $n_{2}$ Si are non magnetic [24]. Because of the sharp Ferm i surface of A  $l_{r}$   $l_{TM}$  -TM oscillated (Friedel oscillations of the charge density). It asymptotic form at large TM-TM distance (r) is of the form:

$$_{\text{TM -TM}}$$
 (r) /  $\frac{\cos(2k_F r)}{r^3}$ : (4)

The phase shift depends on the nature of the TM atom and varies from 2 to 0 as the d band lls. Magnitude of the medium range interaction is larger for M n-M n than for other transition metal (Cr, Fe, Co, Ni, Cu), because the number of delectrons close to  $E_{\rm F}$  is the largest for Mn, and the most delocalized electrons are electrons with Ferm i energy. The e ect analysed here is then more important for Al-rich alloys containing Mn element than for alloys containing other TM elements.

The total DOS of two M n atoms in the free electrons matrix is:

$$n (E ;r) = n_{sp}^{0} (E) + n_{2M n} (E ;r);$$
 (5)

where  $n_{\rm sp}^0$  is the free electron DOS and  $n_{\rm 2M~n}$ , the variation of the total DOS due to two Mn atoms.  $n_{\rm 2M~n}$  depends on the Mn-Mn distance r. When r is very large (almost in nity), each Mn are similar to Mn in purity thus:  $n_{\rm 2M~n}$  =

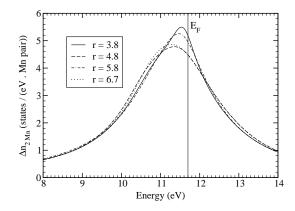


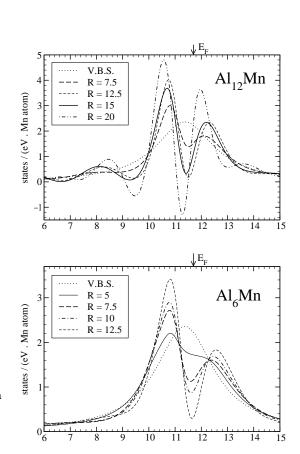
Fig. 2: Variation of the DOS,  $n_{2M~n}$  (E), due to 2 M n impurities in free electrons matrix. The M n-M n distances  $r=3.8\,\mathrm{A}$  and  $r=5.8\,\mathrm{A}$  correspond to positive M n-M n interaction, whereas  $r=4.8\,\mathrm{A}$  and  $r=6.7\,\mathrm{A}$  correspond to minima of the interaction (see arrows on Fig. 1).

2  $n_{1M~n}$ , where  $n_{1M~n}$  is the wellknown Lorentzian of the virtual-bound states. But small deviation from the Lorentzian occurs for niter. On Fig.2,  $n_{2M~n}$  (E) is drawn for dierent values of r. r =  $3.8\,\mathrm{A}$  and r =  $5.8\,\mathrm{A}$  correspond to positive values of M n-M n interaction (Fig.1). These distances are thus unstable and the corresponding DOSs at E  $_{\mathrm{F}}$  increase with respect to Lorentzian value. On the other hand, r =  $4.8\,\mathrm{A}$  and r =  $6.7\,\mathrm{A}$  are m ore stable (m in im a of interaction), and the corresponding DOSs at E  $_{\mathrm{F}}$  are lower than the Lorentzian value.

## 4. E ect of M n sub-lattice on electronic structure of approxim ants

### 4.1. Density of states

In this section, the e ect of indirect M n-M n interaction on the DOS of approximants is analysed. We focus on the case of cubic A  $l_{12}$ M n, orthorhombic o-A  $l_6$ M n and cubi -A  $l_9$ M  $n_2$ Si. In each of these phases, M n sites are similar and



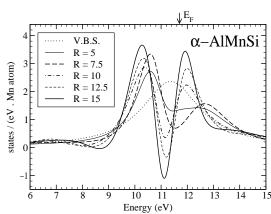


Fig. 3: Variation of the DOS due to Mn sublattice,  $n_R$  (E), in A  $l_{12}$ Mn, o-A  $l_{2}$ Mn and -A  $l_{2}$ Mn $_{2}$ Si. These calculations include e ects of all Mn-Mn pairs up to Mn-Mn distance equal to R (R in A). VBS. is the Lorentzian of one Mn im purity in the free electron matrix (virtual-bound state).

Mn atoms are not rst-neighbour. In metallic alloys, the main aspects of the DOS are consequences of short range and medium range atom ic order. The elect of the medium range order on the pseudogap at Fermi energy is estimated from a simple model that takes only into account the Mn-Mn paire ects with Mn-Mn distances larger than rst-neighbour distances. An important question is to determine the distance up to which an indirect Mn-Mn interaction is essential.

A ssum ing a Hum e-R othery mechanism for the stabilization, the electronic energy is a sum of pair interaction. As interaction magnitudes are larger for M n-M n than for A l-M n and A l-A l [27], M n-M n has a major e ect on the electronic energy and A l-A l, A l-M n are neglected. Triplet e ects, quadruplet e ects (...), that might be important for a transition metal concentration larger than 25% [28], are neglected. In this model, the total D O S,  $n_R$  (E), is calculated as the sum of the variation of the D O S due to each M n-M n pair:

$$n_{R} (E) = n_{sp}^{0} (E) + n_{R} (E);$$
 (6)  
 $n_{R} (E) = x n_{1M n} (E)$   
 $+ n_{2M n} (E; r_{ij}) 2 n_{1M n} (E)$  (7)

where i, j are index of M n atom,  $r_{ij}$  is M  $n_i$ -M  $n_j$  distance, and x, the number of M n atom s.  $n_{2M\ n}$  is de ned by equation (5).  $n_{1M\ n}$  is the variation of the DOS due to one M n impurity in the free electron matrix: virtual-bound state (V B S.).  $n_{1M\ n}$  is a Lorentzian centred at energy E d with a width at half maximum equal to 2 .  $n_R$  is the total DOS computed by taking into account all M n-M n interaction up to M n-M n distance equal to R .  $n_R$  is the part of  $n_R$  due to M n atom s.

 $n_R$  (E ) of A  $l_12\text{M}$  n, o-A  $l_6\text{M}$  n and -A  $l_9\text{M}$   $n_2\text{Si}$  are shown in Fig.3 for dierent values of distance R . First M n-M n distance is 6.47A in A  $l_12\text{M}$  n, 4.47A in o-A  $l_6\text{M}$  n and 4.61 A in -A  $l_9\text{M}$   $n_2\text{Si}$ , but a well-pronounced pseudogap appeared only when the M n-M n interactions up to 10-20A are taken into account.

N egative value of  $n_R$  (E) induces reduction of the total DOS with respect to the free electron value  $n_{\rm sp}^0$ . For o-A  $l_6M$  n, the minimum of

the pseudogap corresponds to  $n_R$  ' 0. The total DOS at the minimum of the pseudogap is thus similar to pure AlDOS, in agreement with rst-principles calculation [14]. But for Al $_2$ M n and -Al $_9$ M n $_2$ Si, as  $n_R$  < 0, a reduction of the total DOS with respect to free electron case is due to Mn-Mn medium range interaction. First-principles studies [14, 10] have already shown a reduction. The present work enlightens a particular elect of Mn atoms in these ab initio results.

### 4.2. Energy

The \structural energy", E, of the M n sublattice in Alhost is de ned as the energy needed to built the M n sub-lattice in the m etallic host that simulates Al (and Si) host from isolated M n atom s in the same m etallic host. E per unit cell is:

$$E = \sum_{\substack{i;j \ (j \in j)}}^{X} \frac{1}{2} \sum_{M \ n-M \ n} (r_{ij}) e^{\frac{r_{ij}}{L}}; \qquad (8)$$

L is the mean-free path of electrons due to scattering by static disorder or phonons [12]. L depends on the structural quality and temperature and can be estimated to be larger than 10 A . E (L) for A  $l_12M$  n, o-A  $l_2M$  n and  $-A \ l_2M$  n $_2S$  i are shown on Fig.4. E are always negative with magnitude strong enough to give a signicant contribution to the band energy. This result is in good agreement with e ect of M n-M n interactions on the pseudogap as shown previously. A coording to a Hume-Rothery mechanism, one expects that a pseudogap is well pronounced for a large value of £j.

### 5. Conclusion

A simple model is presented that allows to enlighten e ects of M n atoms on the electronic structure in Al(rich)-M n phases related to quasicrystals. It is shown that an indirect M n-M n interaction up to distances 10-20 A is essential in stabilizing, as it creates a H um e-R othery pseudogap close to E  $_{\rm F}$ . The band energy is then m inim ised.

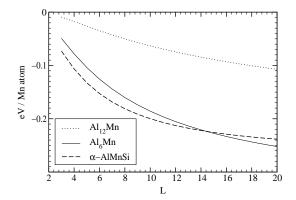


Fig. 4: Structural energy E (L) of M n sub-lattice versus the m ean-free path L (L in A).

The e ect of an indirect M n-M n interactions has been also study in previous works [21, 22, 27, 12, 29]. Recently [12], it explained the origin of a large vacancies in the hexagonal -A  $l_0$ M  $n_3$ Si and  $^\prime$ -A  $l_0$ M  $n_3$  phases, whereas sim ilar site are occupied by M n in A  $l_{4:12}$ M n and A  $l_4$ M n, and by C o in A  $l_5$ C o $_2$ . O n the other hand, m edium range indirect M n-M n interaction is also determ inant for the existence or not of m agnetic m oments in A  $l_1$ M n quasicrystals and approximants [29].

As A l(rich)-M n phase structure are related to those of quasicrystals, it suggests that a Hume-Rothery stabilization, governs by this M n-M n interaction, is intrinsically linked to the emergence of quasiperiodicity.

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